Vishay Semiconductors

650 V Power SiC Gen 3 Merged PIN Schottky Diode, 4 A



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LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS					
I _{F(AV)}	4 A				
V _R	650 V				
V _F at I _F at 25 °C, typ.	1.30 V				
T _J max.	175 °C				
I _R at V _R at 175 °C	12 µA				
Q _C (V _R = 400 V)	12 nC				
Package	SlimDPAK 2L				
Circuit configuration	Single				

FEATURES

- Creepage and clearance distance 2.8 mm minimum
- Very low profile typical height of 1.3 mm
- Majority carrier diode using Schottky technology on SiC wide band gap material



HALOGEN

FREE

- Improved V_F and efficiency by thin wafer technology
- Positive V_F temperature coefficient for easy paralleling
- Virtually no recovery tail and no switching losses
- Temperature invariant switching behavior
- 175 °C maximum operating junction temperature
- MPS structure for high ruggedness to forward current surge events
- Meets JESD 201 class 2 whisker test
- Meet MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

Wide band gap SiC based 650 V Schottky diode, designed for high performance and ruggedness.

Optimum choice for high speed hard switching and efficient operation over a wide temperature range, it is also recommended for all applications suffering from Silicon ultrafast recovery behavior.

Typical applications include AC/DC PFC and DC/DC ultra high frequency output rectification in FBPS and LLC converters.

MECHANICAL DATA

Case: SlimDPAK 2L

Molding compound meets UL 94 V-0 flammability rating Base P/N-M3 - halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per J-STD-002 and JESD 22-B102

PARAMETER	SYMBOL	NOTES / TEST CONDITIONS	VALUES	UNITS	
Peak repetitive reverse voltage	V _{RRM}		650	V	
Continuous forward current	۱ _F	T _M = 158 °C (DC)	4	А	
DC blocking voltage	V _{DC}		650	V	
Repetitive peak surge current	I _{FRM}	$T_M = 25 \text{ °C}, f = 50 \text{ Hz}, \text{ square wave, DC} = 25 \%$	26	А	
Non-repetitive peak forward surge current	I _{FSM}	$T_M = 25 \text{ °C}, t_p = 10 \text{ ms}, \text{ half sine wave}$	29		
		$T_M = 110 \text{ °C}, t_p = 10 \text{ ms}, \text{ half sine wave}$	26	A	
De la la la destructione	P _{tot} ⁽¹⁾	T _M = 25 °C	57	14/	
		T _M = 110 °C	25	W	
Power dissipation	P _{tot} ⁽²⁾	T _M = 25 °C	71	14/	
		T _M = 110 °C	31	W	
10	∫i ² dt	T _M = 25 °C	4.1	• 2	
l ² t value		T _M = 110 °C	3.3	A ² s	
Operating junction and storage temperatures	T _J ⁽³⁾ , T _{Stg}		-55 to +175	°C	

Notes

⁽¹⁾ Based on maximum R_{th}

(2) Based on typical Rth

The heat generated must be less than the thermal conductivity from junction-to-ambient: $dP_D/dT_J < 1/R_{\theta,JA}$ (3)

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ELECTRICAL SPECIFICATIONS ($T_J = 25 \ ^{\circ}C$ unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
		$I_F = 4 A$	-	1.3	1.5		
Forward voltage	V _F	I _F = 4 A, T _J = 150 °C	-	1.50	1.85	V	
		I _F = 4 A, T _J = 175 °C	-	1.58	-		
		V _R = V _R rated	-	0.2	25		
Reverse leakage current	I _R	$V_R = V_R$ rated, $T_J = 150 \ ^\circ C$	-	4.0	50	μA	
		V _R = V _R rated, T _J = 175 °C	-	12	-		
Total capacitance	С	V _R = 1 V, f = 1 MHz	-	175	-	рF	
		V _R = 400 V, f = 1 MHz	-	21	-	μг	
Total capacitive charge	Q _C	V _R = 400 V, f = 1 MHz	-	12	-	nC	

THERMAL - MECHANICAL SPECIFICATIONS ($T_A = 25 \text{ °C}$ unless otherwise specified)							
PARAMETER SYMBOL TEST CONDITIONS MIN. TYP. MAX. UNI					UNITS		
Thermal resistance, junction-to-mount	R _{thJM}		-	2.1	2.7	°C/W	
Marking device				3C04I	EV07T		

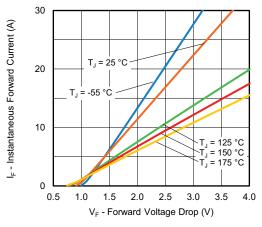


Fig. 1 - Typical Forward Voltage Drop Characteristics

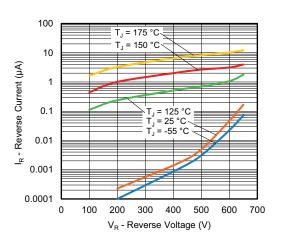


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

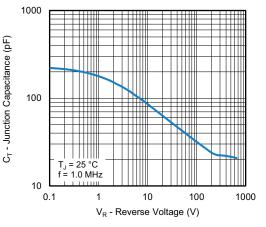


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

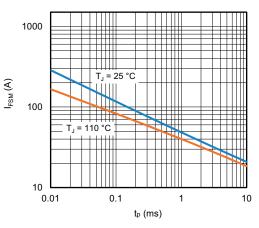
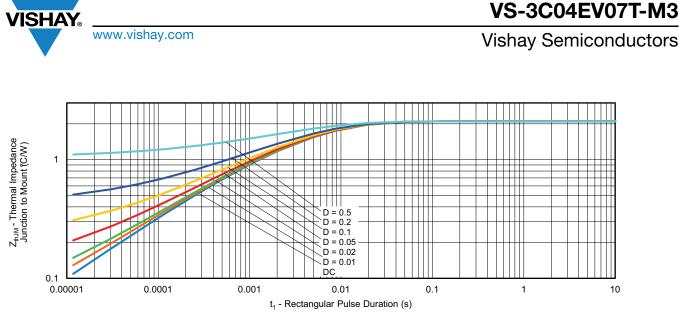


Fig. 4 - Non-Repetitive Peak Forward Surge Current vs. Pulse Duration (Square Wave)

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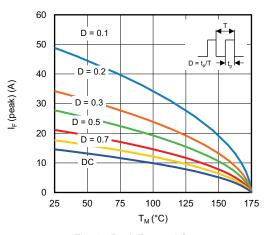


Fig. 6 - Peak Forward Current vs. Maximum Allowable Mount Temperature

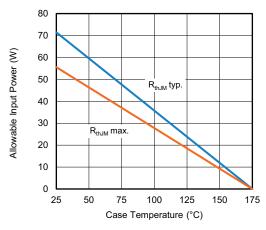


Fig. 7 - Forward Power Loss Characteristics

5 4 Capacitive Energy (µJ) 3 2 T₁ = 25 °C 1 C V dV $E_{-} =$ 0 100 200 300 400 500 600 700 0 Reverse Voltage (V)

Fig. 8 - Typical Capacitive Energy vs. Reverse Voltage

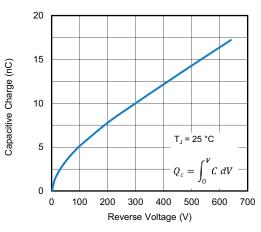


Fig. 9 - Typical Capacitive Charge vs. Reverse Voltage

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ORDERING INFORMATION TABLE

Device code	VS-	3C	04	Е	v	07	т	-M3
	1	2	3	4	5	6	7	8
	1	- Visl	nay Sem	nicondu	ctors pr	oduct		
	2	- 3C	= SiC di	iode, Ge	eneratio	n 3		
	3	- Cur	rent rati	ng (04 =	= 4 A)			
	4	- E=	single c	liode				
	5	- Pac	kage Sl	imDPAł	<			
	6	- Vol	tage rati	ng: (07	= 650 V)		
	7	- T=	true 2 p	in				
	8	- Env	rironmer	ntal digit	:			
		-M3	3 = halog	gen-free	e, RoHS	-compli	iant, and	d termir

ORDERING INFORMATION (Example)							
ORDERING P/N	UNIT WEIGHT (g) PACKAGE CODE BASE QUANTITY PACKAGING DESCRIPTION						
VS-3C04EV07T-M3/I	0.20		4500	13"diameter plastic tape and reel			

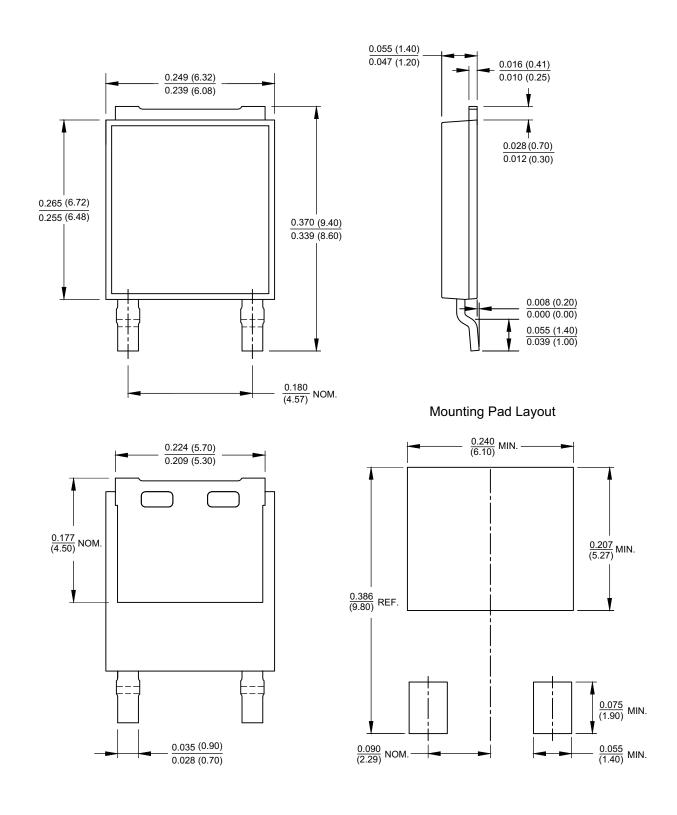
LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?97058</u>					
Part marking information	www.vishay.com/doc?97104				
Packaging information	www.vishay.com/doc?88869				

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SlimDPAK 2L

DIMENSIONS in millimeters (inches)



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